

Substitute form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Sheet

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Of

1

Application Number

Complete if Known

10/706,641

Filing Date

11-12-2003

First Named Inventor

Allen

Group Art Unit

2826

Examiner Name

Unknown

Attorney Docket Number

5308-127DV

U.S. PATENTS AND PATENT PUBLICATIONS

Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
AS ↓ ✓	1.	US-4,803,526		Terada et al.	02-07-1989
	2.	US-5,289,015		Chirovsky et al.	02-22-1994
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Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
AS AS AS	7.	JP	JP360189250 A		Onodera, Tsukasa	09-26-1985	Abstract Only
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	9.	JP	JP411150124 A		Yoshimura et al.	06-02-1999	Abstract Only

Examiner Signature

AT

Date Considered

9/30/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Complete if Known

Application Number	10/706,641
Filing Date	November 12, 2003
First Named Inventor	Scott T. Allen
Group Art Unit	2826
Examiner Name	Ahmed N. Sefer
Attorney Docket Number	5308-127DV

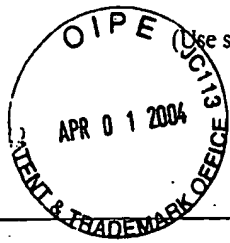
Attorney Docket Number	5308-127DV
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FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number: 5308.127DV		Serial No.: 10/706,641	
LIST OF DOCUMENTS CITED BY APPLICANT <div style="display: flex; align-items: center; justify-content: center;">  (Use several sheets if necessary) </div>							
Applicants: Allen et al.						Filing Date: November 12, 2003	
						Group: 2826	
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Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
AS	1	4,737,469	04/12/88	Stevens	437	33	
↓	2	5,306,650	04/26/94	O'Mara et al.	437	39	
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		Document Number	Date	Country	Class	Subclass	Translation Yes No
AS	4	WO 98/19342	05/07/98	PCT			
AS	5	WO 01/86727	11/15/01	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							

Ex: AS

Date considered: 9/30/05

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					Applicants: Allen, et al.			
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate		
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